Transport on gated C-face epitaxial graphene

CLAIRE BERGER, CNRS-Institut Neel, Grenoble and Georgia Tech, School of Physics, Atlanta

We present transport and electronic properties on single layer and multilayered epitaxial graphene layers grown on 4H-SiC-(000-1) (C-face) by the Confinement Controlled Sublimation method [1]. Single layers present all the characteristics of isolated graphene layers. In particular quantum Hall effect plateaus develop at half-integer values, concomitant with vanishing longitudinal resistivity. High mobility up to $\mu=14,000 \text{ cm}^2/\text{V.s}$ at 300 K is achieved despite contamination and substrate steps. Multilayered epitaxial graphene (MEG) on the C-face consists of non-graphitic rotationally stacked graphene layers, exhibiting the band structure of a single graphene layer [2]. Transport in MEG presents also graphene characteristics. In some cases transport anomalies are observed indicating a much richer picture.